

## Band Switching Diode

- **Applications**

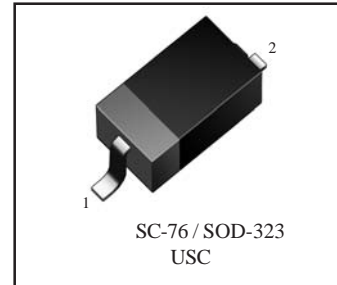
High frequency switching

- **Features**

- 1) Small surface mounting type.
- 2) High reliability.
- 3) We declare that the material of product compliance with RoHS requirements.

- **Construction**

Silicon epitaxial planar



### Device Marking

FDS356 = B
------------

### Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	$V_R$	35	V
DC forward current	$I_F$	100	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55~+125	°C

### Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	–	–	1.0	V	$I_F=10\text{mA}$
Reverse current	$I_R$	–	–	10	nA	$V_R=25\text{V}$
Capacitance between terminals	$C_T$	–	–	1.2	pF	$V_R=6\text{V}, f=1\text{MHz}$
Forward operating resistance	$r_F$	–	–	0.9	$\Omega$	$I_F=2\text{mA}, f=100\text{MHz}$

### Ordering Information

Device	Marking	Shipping
FDS356	B	3000/Tape&Reel

Electrical characteristic curves ( $T_a=25^\circ\text{C}$ )

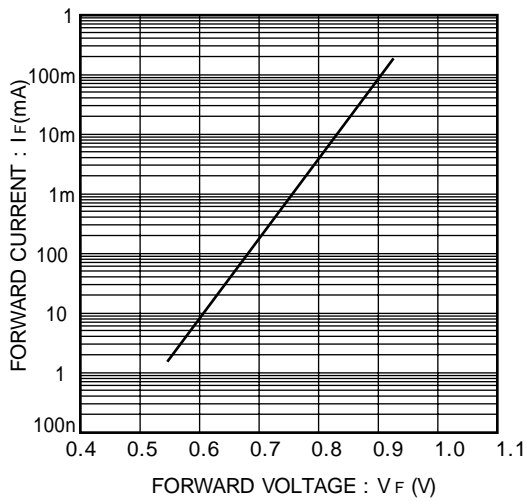


Fig. 1 Forward characteristics

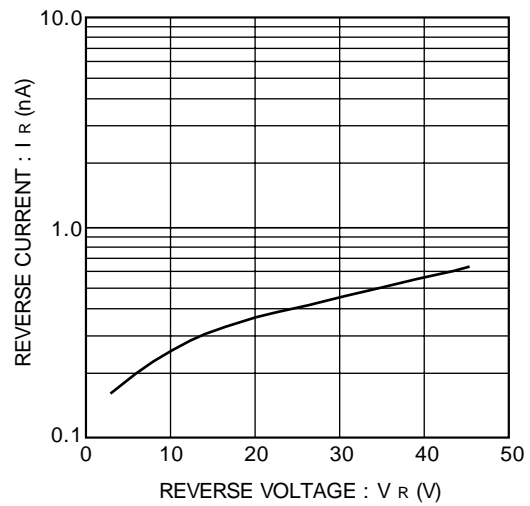


Fig. 2 Reverse characteristics

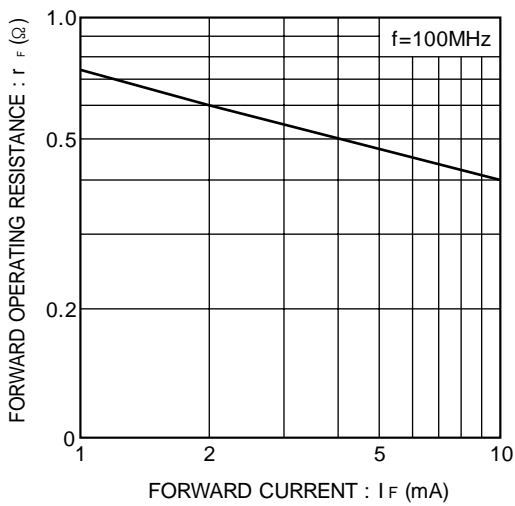


Fig. 4 Forward operating resistance characteristics

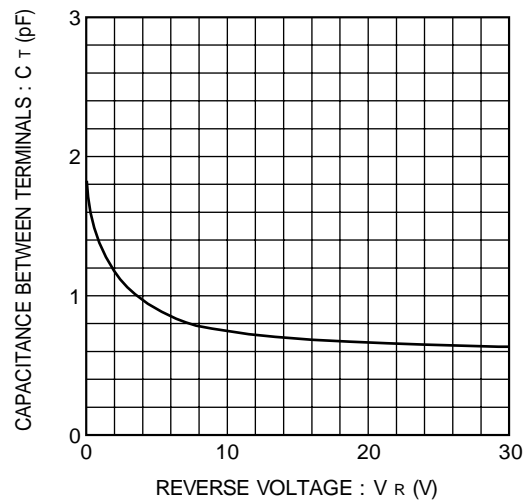
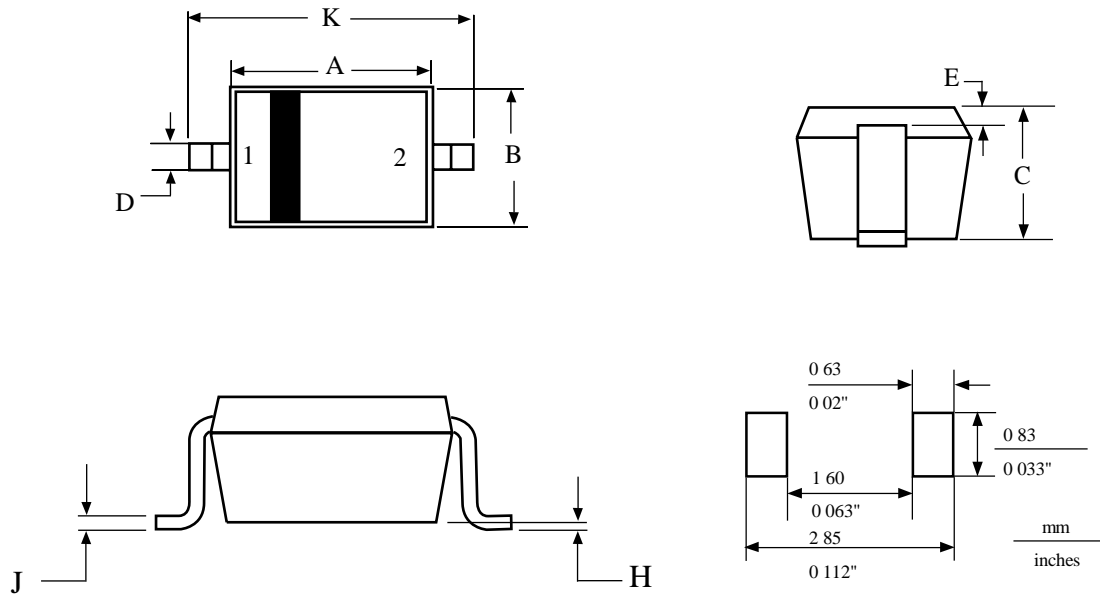


Fig. 3 Capacitance between terminals characteristics

## SC-76 / SOD-323



**NOTES:**

1. DIMENSIONING AND TOLERANCING  
PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
b	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106

PIN:1:CATHODE  
2:ANODE